

**Electronic Supplemental Information (ESI):
Impact of Growth Method on the Structural and Electronic
Properties of Nb:Bi₂WO₆ Thin Films for High-Power pn
Junction Applications**

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This PDF file includes:

Figures S1, and S2

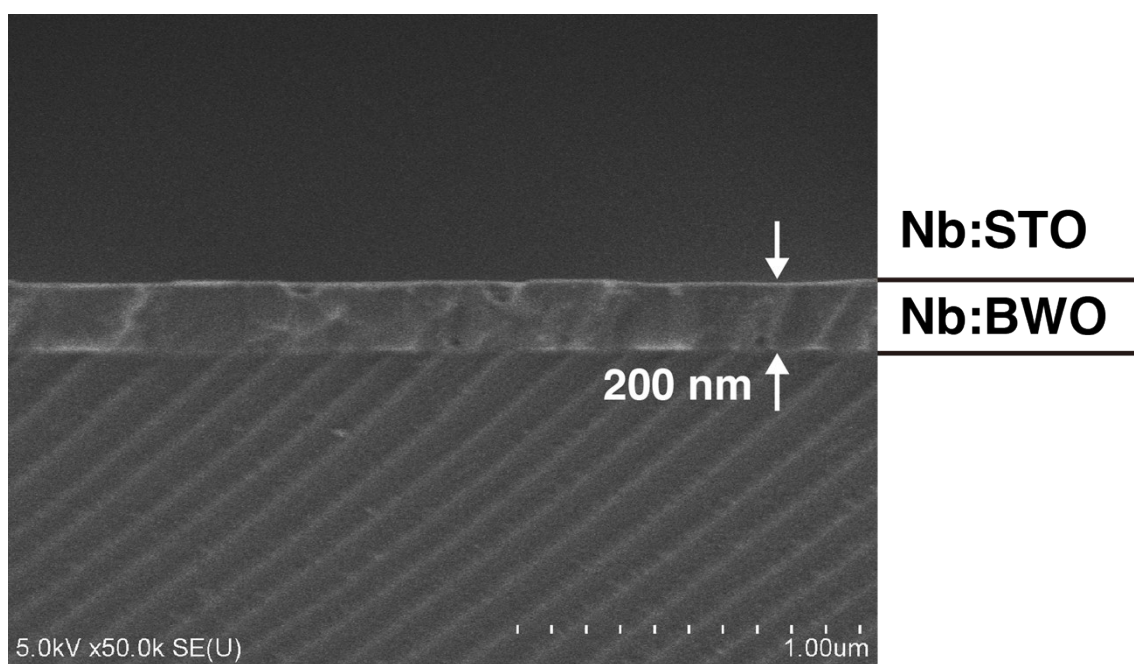


Figure S1. Cross-sectional field emission scanning microscopy (FE-SEM) image of Nb:BWO film grown on Nb:STO substrate.

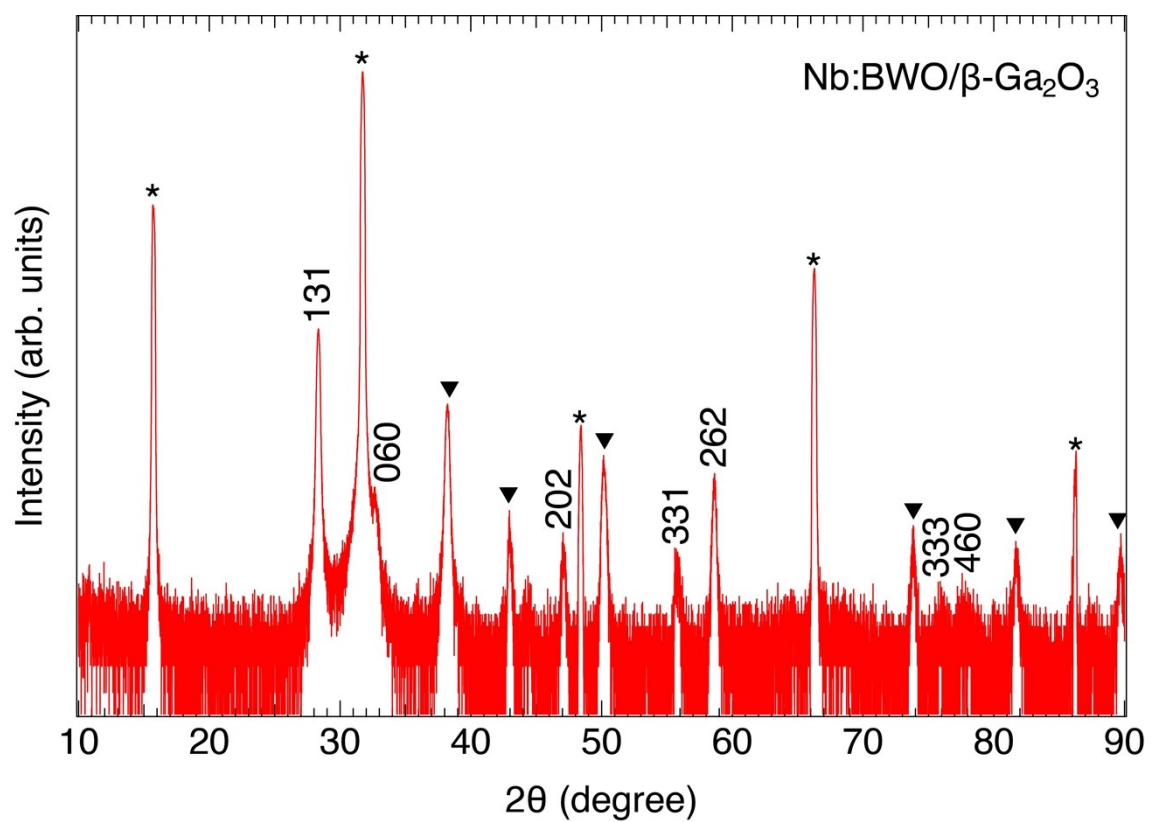


Figure S2. XRD pattern of Nb:BWO film grown on β -Ga₂O₃ substrate. Asterisks and triangles correspond to β -Ga₂O₃ substrate and Cu/Ti/Au electrodes, respectively.